

PRM016N10CT

PFC Device Corporation

100V Single N-Channel MOSFET

Major ratings and characteristics

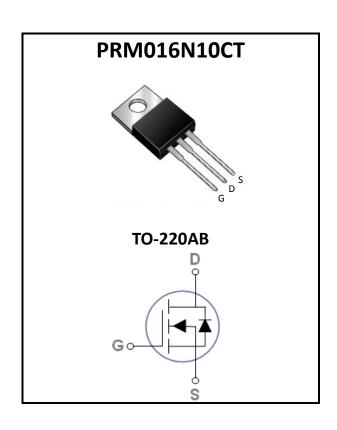
Characteristics	Values	Units
V_{DS}	100	٧
$I_D^5 (T_C=25^{\circ}C)$	65	Α
Max. R _{DS(ON)} @V _{GS} =10V	16	mΩ
Max. R _{DS(ON)} @V _{GS} =4.5V	20	mΩ
T _J Operating Junction Temperature	-55 to +150	လူ

General Description

The N-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. The device is well suited for high efficiency fast switching applications.

Typical Applications

- Charger Adapter
- Power Tools
- LED Lighting



Features

- Max. $R_{DS(ON)}=16m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- 100% E_{AS} Guaranteed
- Green Device Available

1. Characteristics

Maximum Ratings Characteristics

($T_A = 25$ °C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D^{5}	Drain Current – Continuous (T _C =25°C)	65	Α
ıр	Drain Current – Continuous (T _C =100°C)	41	Α
I_{DM}	Drain Current – Pulsed ¹	262	Α
E _{AS}	Single Pulse Avalanche Energy ²	9.9	mJ
I _{AS}	Single Pulse Avalanche Current ²	14.1	Α
Ь	Power Dissipation (T _C =25°C)	114	W
P _D	Power Dissipation – Derate above 25°C	0.9	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient		62	°C/W
$R_{ heta JC}$	Thermal Resistance Junction to Case		1.1	°C/W



Version 4.0 2 / 7

Electrical Characteristics

($T_J = 25$ °C unless otherwise specified)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100			V
	V _{DS} =100V, V _{GS} =0V, T _J =25°C			1	uA	
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =125°C			100	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm20V, V_{DS}=0V$			±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A		14	16	mΩ
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =10A	-	17	20	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_{D}=250uA$	1.0	1.7	2.5	V
g fs	Forward Transconductance	V_{DS} =5V, I_{D} =10A	-	30		S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{3,4}		 19	
Q_gs	Gate-Source Charge ^{3,4}	V _{DS} =50V, V _{GS} =10V, I _D =5A	 2.9	 nC
Q_gd	Gate-Drain Charge ^{3, 4}		 4.5	
$T_{d(on)}$	Turn-On Delay Time ^{3, 4}		 5	
T _r	Turn-On Rise Time ^{3, 4}	V_{DD} =50V, V_{GS} =10V, R_{G} =6.2 Ω	 19	 ns
$T_{d(off)}$	Turn-Off Delay Time ^{3, 4}		 26	 115
T_f	Turn-Off Fall Time ^{3, 4}		 52	
C_{iss}	Input Capacitance		 996	
C_{oss}	Output Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	 197	 pF
C_{rss}	Reverse Transfer Capacitance		 23	
R_{g}	Gate resistance	V_{GS} =0V, V_{DS} =0V, f=1MHz	 0.5	 Ω

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	V_{GS} =0V, I_{S} =20A			1.2	V
t _{rr}	Reverse Recovery Time	I _s =1A, di/dt=100A/us	1	38	1	ns
Q_{rr}	Reverse Recovery Charge	I _S = IA, di/dl= IOOA/dS		29	-	nC

Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. VDD=50V, VGS=10V, L=0.1mH, RG=25 Ω , Starting TJ=25 $^{\circ}$ C
- 3. The data tested by pulsed, pulse width ≤300us, duty cycle ≤2%.
- 4. Essentially independent of operating temperature.
- 5. Silicon limited.

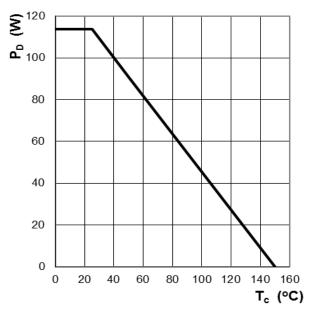


Version 4.0 3 / 7

2. Characteristics Curves

Ratings and Characteristics Curves

(T_A = 25°C unless otherwise specified)



₹ 70 60 50 40 30 20 10 0 25 50 75 100 125 150 T_c (°C)

Figure 1: Power Dissipation

Figure 2: Continuous Drain Current vs. T_C

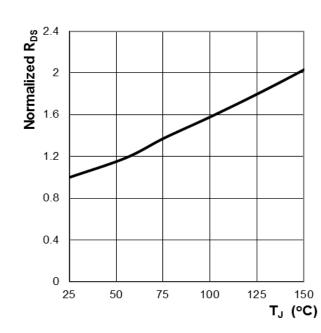


Figure 3: Normalized R_{DS(ON)} vs. T_J

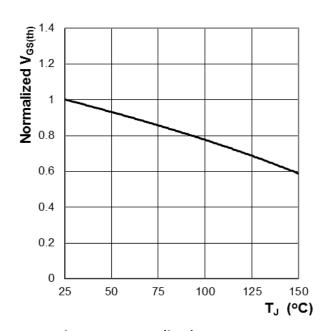


Figure 4: Normalized $V_{GS(th)}$ vs. T_J



Version 4.0 4 / 7

Ratings and Characteristics Curves

($T_A = 25^{\circ}C$ unless otherwise specified)

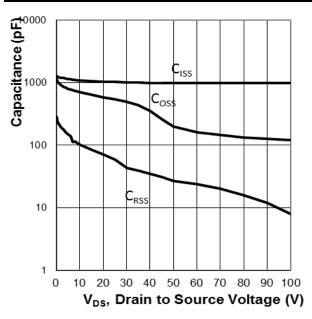


Figure 7: Typ. Capacitance Characteristics

Figure 8: Typ. Gate Charge Characteristics

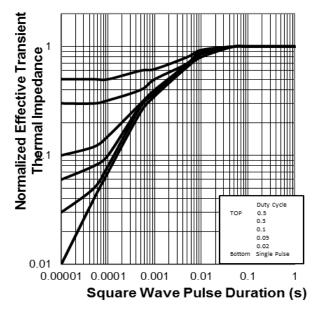


Figure 9: Normalized Thermal Transient Impedance, Junction-to-Case

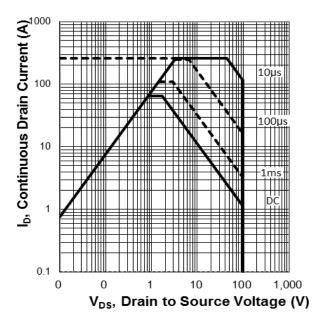


Figure 10: Maximum Safe Operation Area



Version 4.0 5 / 7

3. Marking information

Top Marking Rule

PFC PRM 016N10CT YYWW ABSH

PRM016N10CT = Product Type Marking Code

YYWW = Date Code

YY = Last two digits of year

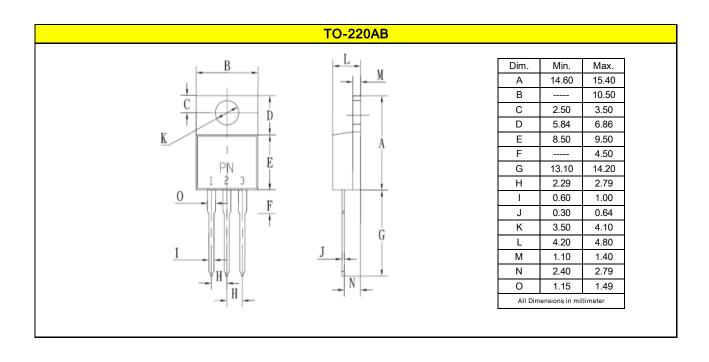
WW = Week code

ABS = Assembly code

H = Halogen Free (N/A = common molding compound)

4. Package information

Package Outline Dimensions millimeters





Version 4.0 6 / 7

5. Ordering information

Part Number	Package	Delivery mode
PRM016N10CT	TO-220AB	50 pcs / Tube

Mechanical

Molder Plastic: UL Flammability Classification Rating 94V-0
Device Weight: 0.07 ounces (1.96grams) - TO-220AB

■ Mounting Torque : Recommended 4~5 kg-cm

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Version 4.0 7 / 7